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12/26/01

PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10025459	12/26/2001	438	200 ⁺	28124	H. PHAM

****APPLICANTS:** Lee Yueh-Chuan; Chen Shih-Lung; Huang Jin-Shing; Lee Wen-Sheng;

****CONTINUING DATA VERIFIED:** *HI?*
None

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**** FOREIGN APPLICATIONS VERIFIED:** *HI?*
None

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed	<input type="checkbox"/> yes <input checked="" type="checkbox"/> no	ATTORNEY DOCKET NO
35 USC 119 conditions met	<input type="checkbox"/> yes <input checked="" type="checkbox"/> no	0941-0382P
Verified and Acknowledged Examiners's initials <i>Waylan HI?</i>		
TITLE : Method of forming a capacitor dielectric structure		

U S DEPT. OF COMM /PAT. & TM-PTO-435L (Rev. 12-94)

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G.
Assistant Examiner		DRAWING	
		Sheets Drwg.	Figs. Drwg.
Primary Examiner		Print Fig.	
PREPARED FOR ISSUE		Application Examiner	
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